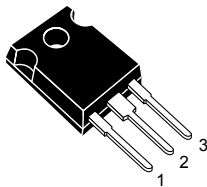
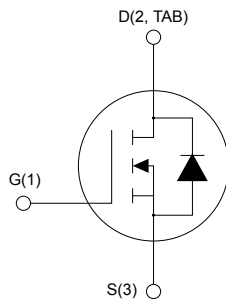


N-channel 600 V, 92 mΩ typ., 31.5 A MDmesh II Power MOSFET in a TO-247 package



TO-247



AM01475v1_noZen



Product status link

[STW34NM60N](#)

Product summary

Order code	STW34NM60N
Marking	34NM60N
Package	TO-247
Packing	Tube

Features

Order code	V _{DS}	R _{DS(on)} max.	I _D
STW34NM60N	600 V	105 mΩ	31.5 A

- 100% avalanche tested
- Low input capacitance and gate charge
- Low gate input resistance

Applications

- Switching applications

Description

This device is an N-channel Power MOSFET developed using the second generation of MDmesh technology. This revolutionary Power MOSFET associates a vertical structure to the company's strip layout to yield one of the world's lowest on-resistance and gate charge. It is therefore suitable for the most demanding high efficiency converters.

1 Electrical ratings

Table 1. Absolute maximum ratings

Symbol	Parameter	Value	Unit
V_{DS}	Drain-source voltage	600	V
V_{GS}	Gate-source voltage	± 25	V
I_D	Drain current (continuous) at $T_C = 25\text{ }^{\circ}\text{C}$	31.5	A
I_D	Drain current (continuous) at $T_C = 100\text{ }^{\circ}\text{C}$	20	A
$I_{DM}^{(1)}$	Drain current (pulsed)	126	A
P_{TOT}	Total power dissipation at $T_C = 25\text{ }^{\circ}\text{C}$	250	W
$dv/dt^{(2)}$	Peak diode recovery voltage slope	15	V/ns
$dv/dt^{(3)}$	MOSFET dv/dt ruggedness	50	V/ns
T_J	Maximum operating junction temperature	150	$^{\circ}\text{C}$
T_{stg}	Storage temperature range	-55 to 150	

1. Pulse width limited by safe operating area.
2. $I_{SD} \leq 31.5\text{ A}$, $di/dt \leq 400\text{ A}/\mu\text{s}$, $V_{DS}(\text{peak}) \leq V_{(BR)DSS}$, $V_{DD} = 480\text{ V}$.
3. $V_{DD} \leq 480\text{ V}$.

Table 2. Thermal data

Symbol	Parameter	Value	Unit
R_{thJC}	Thermal resistance, junction-to-case	0.5	$^{\circ}\text{C}/\text{W}$
R_{thJA}	Thermal resistance, junction-to-ambient	50	$^{\circ}\text{C}/\text{W}$

Table 3. Avalanche characteristics

Symbol	Parameter	Value	Unit
I_{AR}	Avalanche current, repetitive or not-repetitive (pulse width limited by T_J max.)	7	A
E_{AS}	Single pulse avalanche energy (starting $T_J = 25\text{ }^{\circ}\text{C}$, $I_D = I_{AR}$, $V_{DD} = 50\text{ V}$)	345	mJ

2 Electrical characteristics

(T_{CASE} = 25 °C unless otherwise specified)

Table 4. On/off states

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
V _{(BR)DSS}	Drain-source breakdown voltage	I _D = 1 mA, V _{GS} = 0 V	600	-	-	V
I _{DSS}	Zero gate voltage drain current	V _{GS} = 0 V, V _{DS} = 600 V	-	-	1	μA
		V _{GS} = 0 V, V _{DS} = 600 V, T _C = 125 °C ⁽¹⁾	-	-	100	μA
I _{GSS}	Gate body leakage current	V _{DS} = 0 V, V _{GS} = ±25 V	-	-	±100	nA
V _{GS(th)}	Gate threshold voltage	V _{DS} = V _{GS} , I _D = 250 μA	2	3	4	V
R _{DS(on)}	Static drain-source on-resistance	V _{GS} = 10 V, I _D = 14.5 A	-	92	105	mΩ

1. Specified by design, not tested in production.

Table 5. Dynamic

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
C _{iss}	Input capacitance	V _{DS} = 100 V, f = 1 MHz, V _{GS} = 0 V	-	2722	-	pF
C _{oss}	Output capacitance		-	173	-	pF
C _{rss}	Reverse transfer capacitance		-	1.75	-	pF
C _{oss eq.} ⁽¹⁾	Equivalent capacitance time related	V _{DS} = 0 to 480 V, V _{GS} = 0 V	-	458	-	pF
R _g	Intrinsic gate resistance	f = 1 MHz open drain	-	2.9	-	Ω
Q _g	Total gate charge	V _{DD} = 480 V, I _D = 31.5 A, V _{GS} = 0 to 10 V (see the Figure 14. Test circuit for gate charge behavior)	-	84	-	nC
Q _{gs}	Gate-source charge		-	14	-	nC
Q _{gd}	Gate-drain charge		-	45	-	nC

1. C_{oss eq.} is defined as a constant equivalent capacitance giving the same charging time as C_{oss} when V_{DS} increases from 0 to 80% V_{DSS}.

Table 6. Switching times

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
t _{d(on)}	Turn-on delay time	V _{DD} = 300 V, I _D = 15.75 A, R _G = 4.7 Ω V _{GS} = 10 V	-	18	-	ns
t _r	Rise time		-	36	-	ns
t _{d(off)}	Turn-off delay time	(see the Figure 13. Test circuit for resistive load switching times and Figure 18. Switching time waveform)	-	104	-	ns
t _f	Fall time		-	73	-	ns

Table 7. Source-drain diode

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
I_{SD}	Source-drain current		-	-	31.5	A
$I_{SDM}^{(1)}$	Source-drain current (pulsed)		-	-	126	A
$V_{SD}^{(2)}$	Forward on voltage	$I_{SD} = 31.5 \text{ A}$, $V_{GS} = 0 \text{ V}$	-	-	1.6	V
t_{rr}	Reverse recovery time	$I_{SD} = 31.5 \text{ A}$, $di/dt = 100 \text{ A}/\mu\text{s}$, $V_{DD} = 60 \text{ V}$ (see the Figure 15. Test circuit for inductive load switching and diode recovery times)	-	412	-	ns
Q_{rr}	Reverse recovery charge		-	8	-	μC
I_{RRM}	Reverse recovery current		-	39	-	A
t_{rr}	Reverse recovery time	$I_{SD} = 31.5 \text{ A}$, $di/dt = 100 \text{ A}/\mu\text{s}$, $V_{DD} = 60 \text{ V}$ $T_J = 150 \text{ }^\circ\text{C}$ (see the Figure 15. Test circuit for inductive load switching and diode recovery times)	-	490	-	ns
Q_{rr}	Reverse recovery charge		-	10	-	μC
I_{RRM}	Reverse recovery current		-	43	-	A

1. Pulse width limited by safe operating area.
2. Pulsed: pulse duration = 300 μs , duty cycle 1.5%.

2.1 Electrical characteristics (curves)

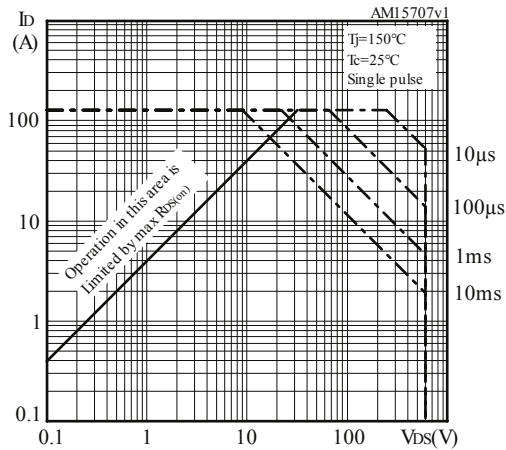
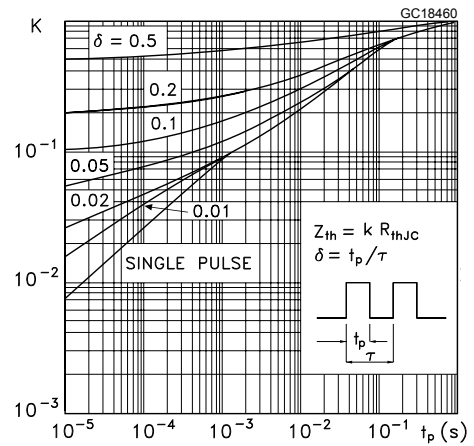
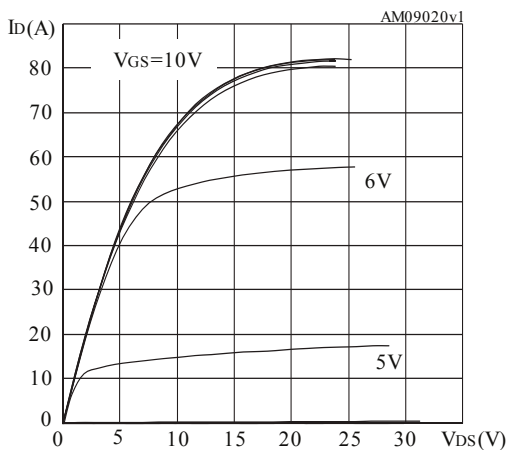
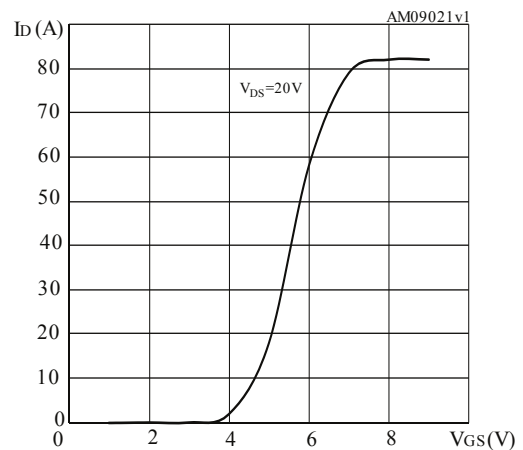
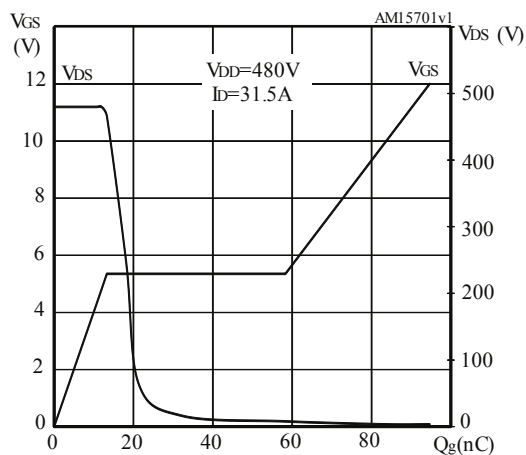
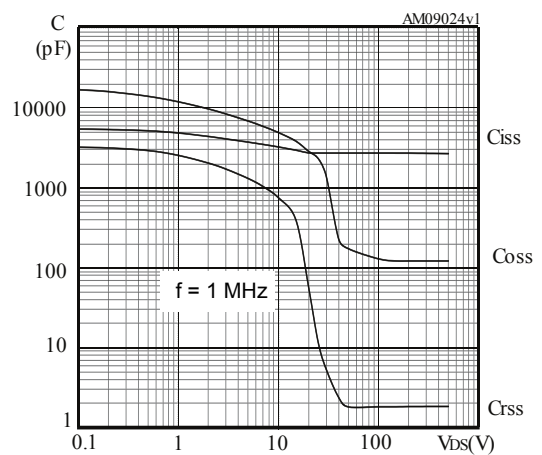
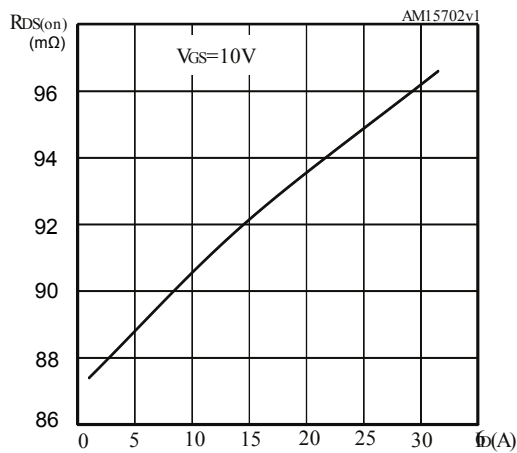
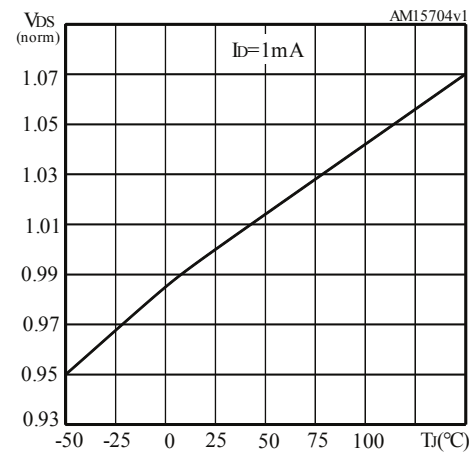
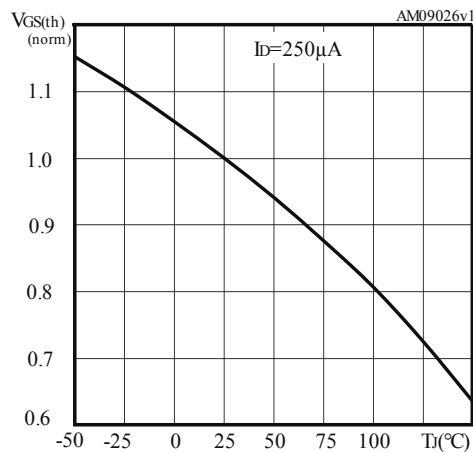
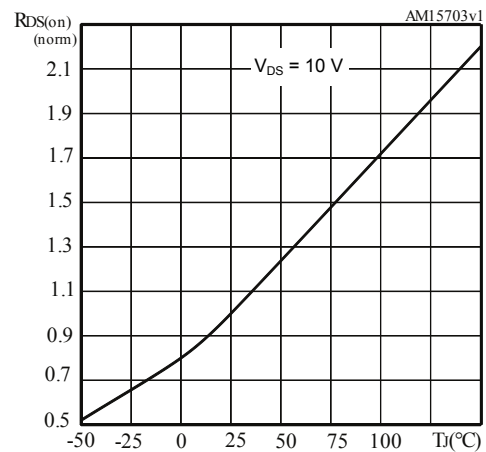
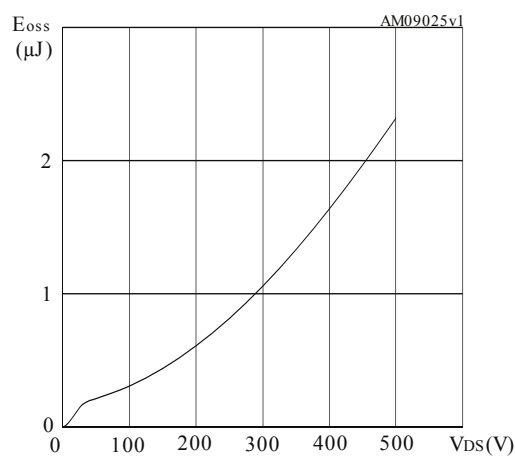
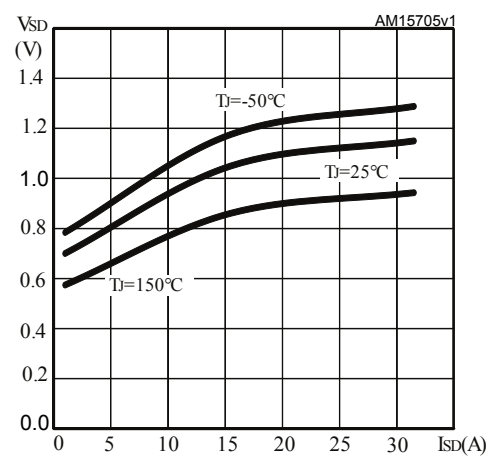
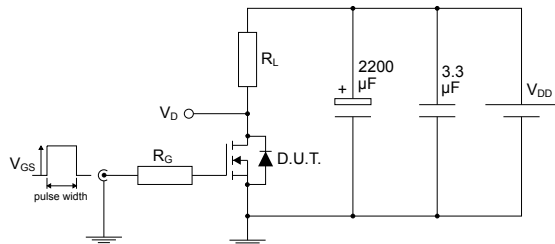
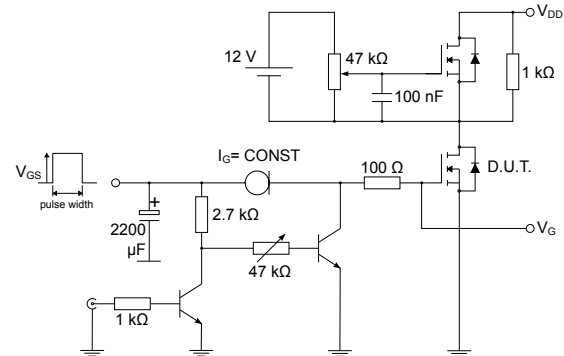
Figure 1. Safe operating area

Figure 2. Normalized transient thermal impedance

Figure 3. Typical output characteristics

Figure 4. Typical transfer characteristics

Figure 5. Typical gate charge characteristics

Figure 6. Typical capacitance characteristics


Figure 7. Typical drain-source on-resistance

Figure 8. Normalized breakdown voltage vs temperature

Figure 9. Normalized gate threshold vs temperature

Figure 10. Normalized on-resistance vs temperature

Figure 11. Typical output capacitance stored energy

Figure 12. Typical reverse diode forward characteristics


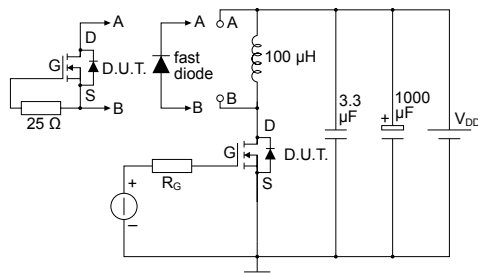
3 Test circuits

Figure 13. Test circuit for resistive load switching times


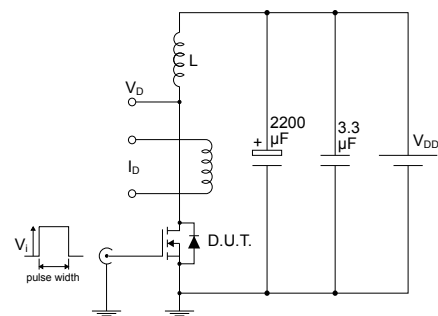
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Figure 14. Test circuit for gate charge behavior


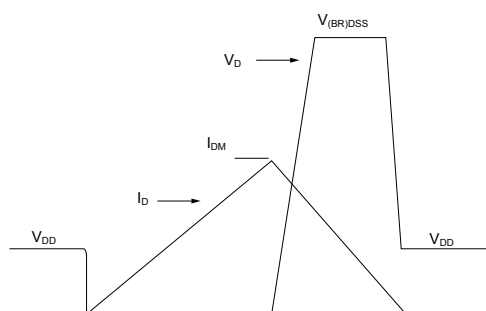
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Figure 15. Test circuit for inductive load switching and diode recovery times


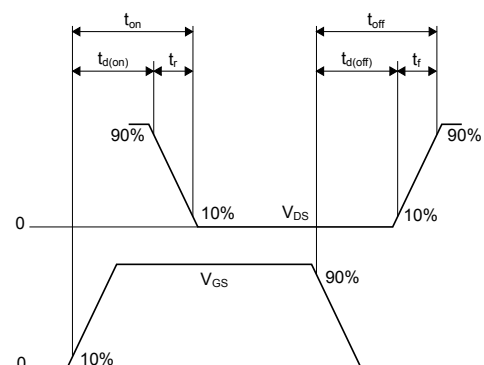
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Figure 16. Unclamped inductive load test circuit


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Figure 17. Unclamped inductive waveform


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Figure 18. Switching time waveform


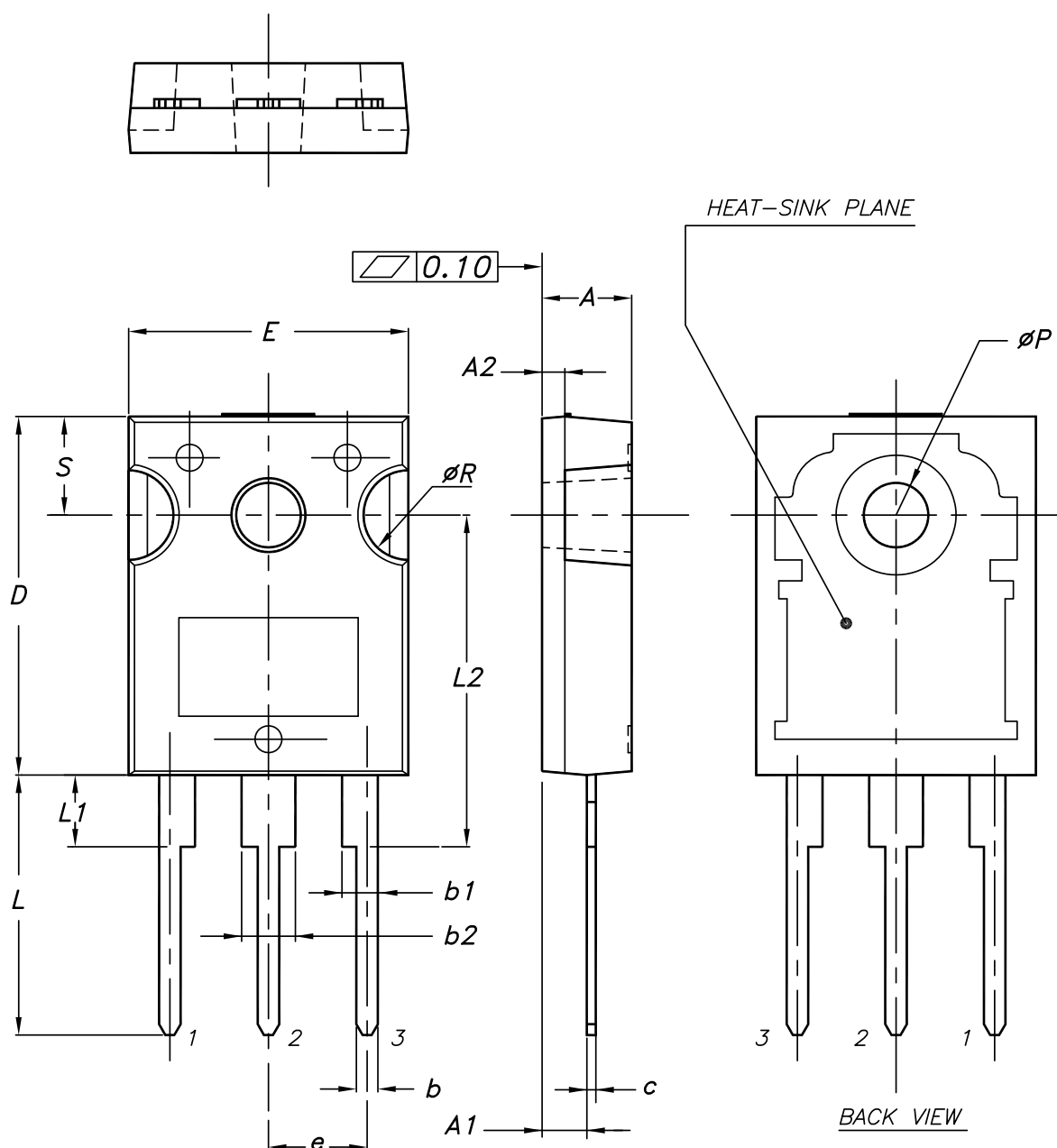
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4 Package information

To meet environmental requirements, ST offers these devices in different grades of **ECOPACK** packages, depending on their level of environmental compliance. ECOPACK specifications, grade definitions, and product status are available at: www.st.com. ECOPACK is an ST trademark.

4.1 TO-247 package information

Figure 19. TO-247 package outline



0075325_11

Table 8. TO-247 package mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	4.85		5.15
A1	2.20		2.60
A2		1.27	
b	1.0		1.40
b1	2.0		2.40
b2	3.0		3.40
c	0.40		0.80
D	19.85		20.15
E	15.45		15.75
e	5.30	5.45	5.60
L	14.20		14.80
L1	3.70		4.30
L2		18.50	
ØP	3.55		3.65
ØR	4.50		5.50
S	5.30	5.50	5.70

Revision history

Table 9. Document revision history

Date	Revision	Changes
25-Mar-2015	1	First release.
30-Mar-2015	2	Updated <i>Figure 2: Safe operating area</i> and <i>Figure 3: Thermal impedance</i> .
13-Jan-2026	3	Updated Section 4: Package information . Minor text changes.

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